

<IGBT Modules>

CM1800DW-24ME

**HIGH POWER SWITCHING USE
INSULATED TYPE**



Collector current I_c **1 8 0 0 A**
 Collector-emitter voltage V_{CES} **1 2 0 0 V**
 Maximum junction temperature T_{vjmax} **1 7 5 °C**

- Dual switch (Half-bridge)
- Copper base plate (Nickel-plating)
- Ni-plating signal terminals
- RoHS Directive compliant
- UL Recognized under UL 1557, File No. E323585

APPLICATION

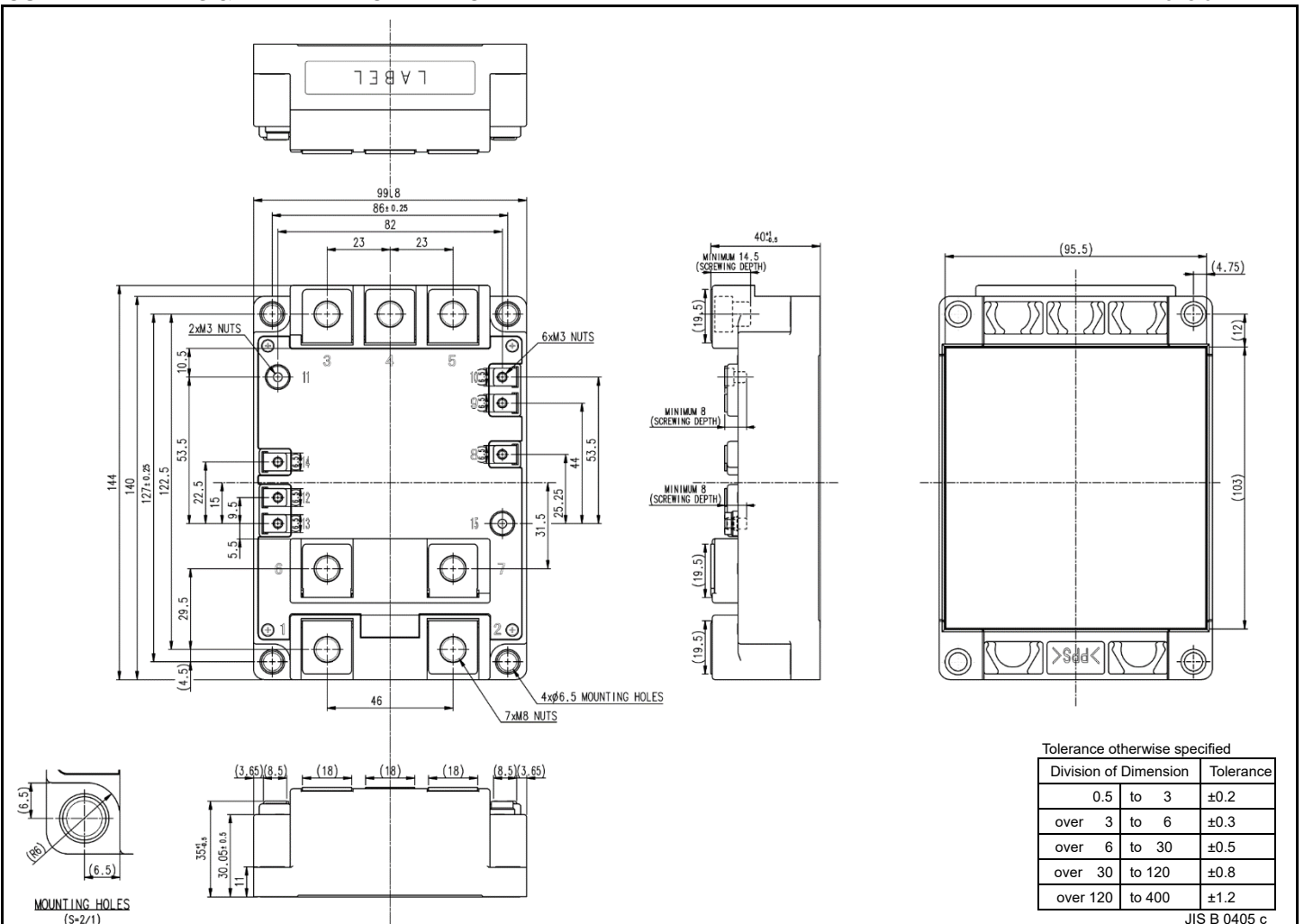
Photovoltaic power converter, Energy storage system, Motion control, etc.

OPTION

- V_{CESat} selection for parallel connection
- PC-TIM (Phase Change Thermal Interface Material) pre-apply

OUTLINE DRAWING & INTERNAL CONNECTION

Dimension in mm

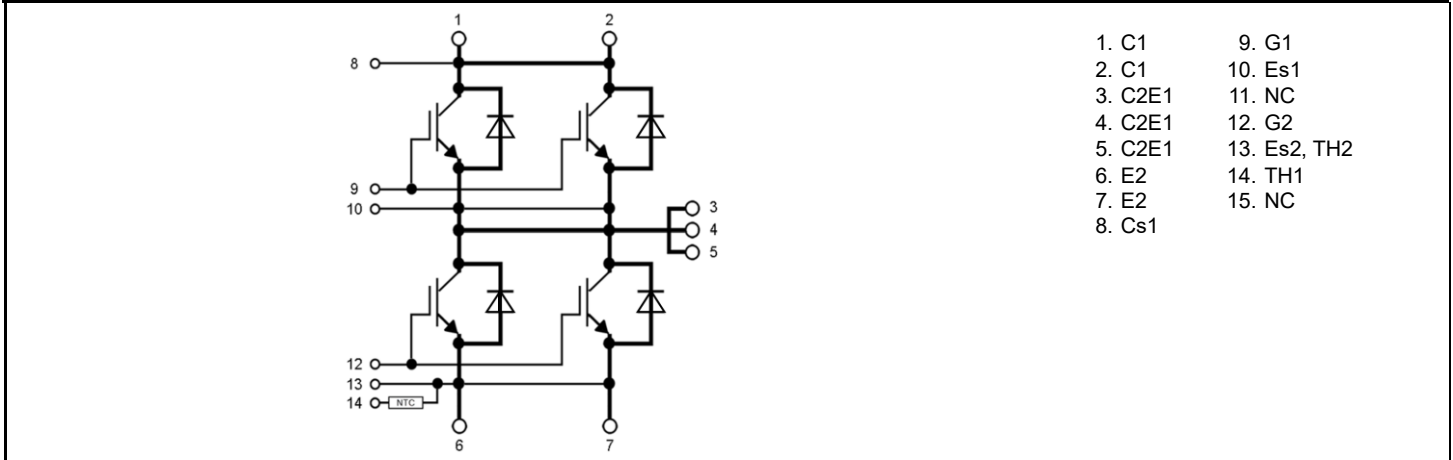


CM1800DW-24ME

HIGH POWER SWITCHING USE
INSULATED TYPE

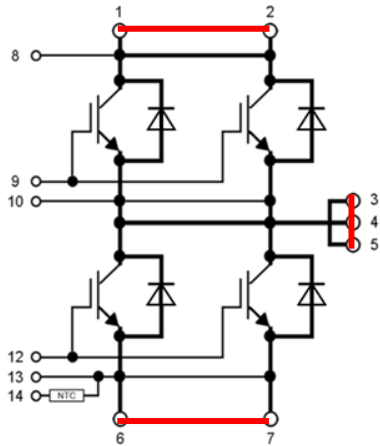
INTERNAL CONNECTION

TERMINAL CODE



NOTE

Terminal 1 and 2, Terminal 3,4 and 5, Terminal 6 and 7,
These terminals should be connected respectively when it is used.



CM1800DW-24MEHIGH POWER SWITCHING USE
INSULATED TYPE**MAXIMUM RATINGS ($T_{vj} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)**

Symbol	Item	Conditions	Rating	Unit
V_{CES}	Collector-emitter voltage	G-E short-circuited	1200	V
V_{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I_C	Collector current	DC (Note2, 4), $T_C = 84\text{ }^{\circ}\text{C}$	1800	A
I_{CRM}		Pulse, Repetitive (Note3)	3600	
P_{tot}	Total power dissipation	$T_C = 25\text{ }^{\circ}\text{C}$ (Note2, 4)	6250	W
I_E (Note1)	Emitter current	DC (Note2), $T_C = 25\text{ }^{\circ}\text{C}$	1800	A
I_{ERM} (Note1)		Pulse, Repetitive (Note3)	3600	
V_{isol}	Isolation voltage	Terminals to base plate, RMS, $f = 60\text{ Hz}$, AC 1 min	4000	V
T_{vjmax}	Maximum junction temperature	Instantaneous event (overload) (Note8)	175	$^{\circ}\text{C}$
T_{cmax}	Maximum case temperature	(Note4,8)	140	$^{\circ}\text{C}$
T_{stg}	Storage temperature	-	-40 ~ 140	$^{\circ}\text{C}$
T_{vjop}	Operating junction temperature	Continuous operation (Note8)	-40 ~ 150	

ELECTRICAL CHARACTERISTICS ($T_{vj} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I_{CES}	Collector-emitter cut-off current	$V_{CE} = V_{CES}$, G-E short-circuited	-	-	1.0	mA	
I_{GES}	Gate-emitter leakage current	$V_{GE} = \pm 20\text{ V}$, C-E short-circuited	-	-	1.0	μA	
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C = 180\text{ mA}$, $V_{CE} = 10\text{ V}$	5.4	6.0	6.6	V	
V_{CEsat}	Collector-emitter saturation voltage	$I_C = 1800\text{ A}$ (Note5) $V_{GE} = 15\text{ V}$, (Terminal)	$T_{vj} = 25\text{ }^{\circ}\text{C}$	-	1.55	1.90	V
			$T_{vj} = 125\text{ }^{\circ}\text{C}$	-	1.75	-	
			$T_{vj} = 150\text{ }^{\circ}\text{C}$	-	1.80	-	
		$I_C = 1800\text{ A}$ (Note5) $V_{GE} = 15\text{ V}$, (Chip)	$T_{vj} = 25\text{ }^{\circ}\text{C}$	-	1.50	1.75	V
			$T_{vj} = 125\text{ }^{\circ}\text{C}$	-	1.70	-	
			$T_{vj} = 150\text{ }^{\circ}\text{C}$	-	1.75	-	
C_{ies}	Input capacitance	$V_{CE} = 10\text{ V}$, G-E short-circuited	-	310	-	nF	
C_{oes}	Output capacitance		-	14	-		
C_{res}	Reverse transfer capacitance		-	8	-		
Q_G	Gate charge	$V_{CC} = 600\text{ V}$, $I_C = 1800\text{ A}$, $V_{GE} = \pm 15\text{ V}$	-	18	-	μC	
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 600\text{ V}$, $I_C = I_E = 1800\text{ A}$, $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 0.47\text{ }\Omega$, $R_{Goff} = 0\text{ }\Omega$ Inductive load	-	-	900	ns	
t_r	Rise time		-	-	200		
$t_{d(off)}$	Turn-off delay time		-	-	2000		
t_f	Fall time		-	-	1000		
V_{EC} (Note1)	Emitter-collector voltage	$I_E = 1800\text{ A}$ (Note5) G-E short-circuited (Terminal)	$T_{vj} = 25\text{ }^{\circ}\text{C}$	-	1.50	1.85	V
			$T_{vj} = 125\text{ }^{\circ}\text{C}$	-	1.55	-	
			$T_{vj} = 150\text{ }^{\circ}\text{C}$	-	1.60	-	
		$I_E = 1800\text{ A}$ (Note5), G-E short-circuited, (Chip)	$T_{vj} = 25\text{ }^{\circ}\text{C}$	-	1.45	1.70	V
			$T_{vj} = 125\text{ }^{\circ}\text{C}$	-	1.50	-	
			$T_{vj} = 150\text{ }^{\circ}\text{C}$	-	1.55	-	
t_{rr} (Note1)	Reverse recovery time	$V_{CC} = 600\text{ V}$, $I_C = I_E = 1800\text{ A}$, $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 0.47\text{ }\Omega$, $R_{Goff} = 0\text{ }\Omega$, Inductive load	-	-	400	ns	
Q_{rr} (Note1)	Reverse recovery charge		-	150	-	μC	
E_{on}	Turn-on switching energy per pulse	$V_{CC} = 600\text{ V}$, $I_C = I_E = 1800\text{ A}$, $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 0.47\text{ }\Omega$, $R_{Goff} = 0\text{ }\Omega$, $T_{vj} = 150\text{ }^{\circ}\text{C}$, $L_G = 15\text{ nH}$ (Note9), Inductive load	di/dt (Note10) $= 12.5\text{ kA}/\mu\text{s}$	-	134	-	mJ
E_{off}	Turn-off switching energy per pulse		dv/dt (Note10) $= 5.6\text{ kV}/\mu\text{s}$	-	197	-	
E_{rr} (Note1)	Reverse recovery energy per pulse		di/dt (Note10) $= 12.5\text{ kA}/\mu\text{s}$	-	140	-	
I_{SC}	Short circuit current	$T_{vj} = 150\text{ }^{\circ}\text{C}$, $V_{CC} = 800\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 0.47\text{ }\Omega$, $t_W \leq 6\text{ }\mu\text{s}$	-	7.0	-	kA	

CM1800DW-24ME

HIGH POWER SWITCHING USE
INSULATED TYPE

NTC THERMISTOR PART

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R_{25}	Zero-power resistance	$T_C = 25\text{ }^\circ\text{C}$ (Note4)	4.85	5.00	5.15	k Ω
$\Delta R/R$	Deviation of resistance	$R_{100} = 493\ \Omega$, $T_C = 100\text{ }^\circ\text{C}$ (Note4)	-7.3	-	+7.8	%
$B_{(25/50)}$	B-constant	Approximate by equation (Note6)	-	3375	-	K
P_{25}	Power dissipation	$T_C = 25\text{ }^\circ\text{C}$ (Note4)	-	-	10	mW

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal resistance	Junction to case, per IGBT switch (Note4)	-	-	24	K/kW
$R_{th(j-c)D}$		Junction to case, per FWD switch (Note4)	-	-	39	
$R_{th(c-s)}$	Contact thermal resistance	Grease, per 1 module	-	10	-	K/kW

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M_t	Mounting torque	Main terminals M 8 screw	7.0	10.5	14.0	N·m
M_t		Auxiliary terminals M 3 screw	0.4	0.5	0.6	N·m
M_s		Mounting to heat sink M 6 screw	3.5	4.0	4.5	N·m

MODULE

Symbol	Item	Conditions	Value	Unit
m	Mass	-	860	g
d_s	Creepage distance	Terminal to terminal	19.2	mm
		Terminal to base plate	34.1	
d_a	Clearance	Terminal to terminal	8.7	mm
		Terminal to base plate	32.2	
R_{CC+EE}	Internal lead resistance	Main terminals - chip, $T_C = 25\text{ }^\circ\text{C}$ (Note4)	0.15	m Ω
L_s	Internal stray inductance	P-N	9	nH
r_g	Internal gate resistance	Per switch	0.33	Ω

*: This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU and (EU)2015/863.

Note 1. Represent ratings and characteristics of the anti-parallel, emitter-collector free-wheeling diode (FWD).

- Junction temperature (T_{vj}) should not increase beyond T_{vjmax} rating.
- Pulse width and repetition rate should be such that the device junction temperature (T_{vj}) dose not exceed T_{vjmax} rating.
- Case temperature (T_C) and heat sink temperature (T_S) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.
- Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.
- $B(25/50) - \ln \left(\frac{R_{25}}{R_{50}} \right) / \left(\frac{1}{T_{25}} - \frac{1}{T_{50}} \right)$
 R_{25} : resistance at absolute temperature T_{25} [K]; $T_{25} = 25\text{ }^\circ\text{C} + 273.15 = 298.15$ [K]
 R_{50} : resistance at absolute temperature T_{50} [K]; $T_{50} = 50\text{ }^\circ\text{C} + 273.15 = 323.15$ [K]
- Reference value. Thermally conductive grease of thermal conductivity $\lambda = 0.9\text{ W/(m}\cdot\text{K)}$ and thickness $D_{(c-s)} = 50\ \mu\text{m}$.
- Long term performance related to thermal conductive grease (including but not limited to aspects such as the increase of thermal resistance due to pumping out, etc.) should be verified under user's specific application conditions. Each temperature condition (T_{vjmax} , T_{vjop} , T_{Cmax}) must be maintained below the maximum rated temperature throughout consideration of the temperature rise even for long term usage.
- L_s represents the inductance of the switching circuit including the power module's inductance, which is calculated from the voltage and current waveforms during the switching.
- 10–90% range of the specified condition.

CM1800DW-24ME

HIGH POWER SWITCHING USE
INSULATED TYPE

RECOMMENDED OPERATING CONDITIONS

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
V_{CC}	(DC) Supply voltage	Applied across C1-E2 terminals	-	600	850	V	
V_{GEon}	Gate-emitter drive voltage	Applied across G1-Es1/G2-Es2 terminals	13.5	15.0	16.5	V	
R_G	External gate resistance	Per switch	On	0.47	-	10	Ω
			Off	0	-	10	Ω

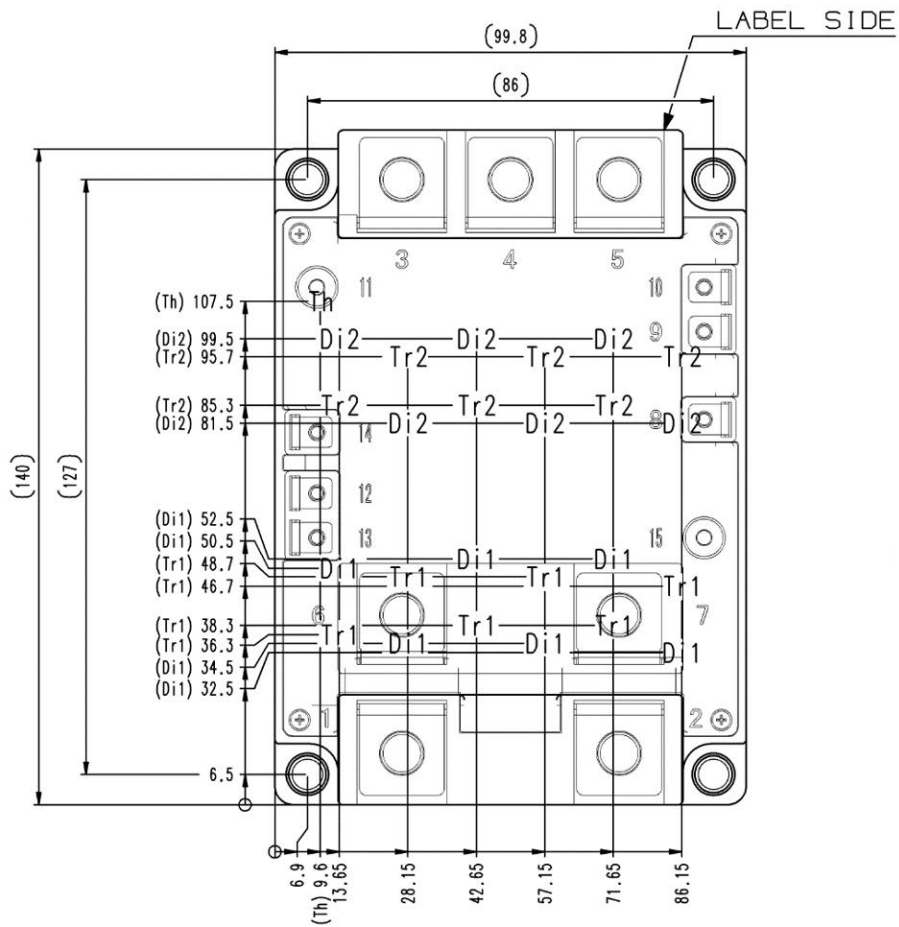
Note • The performance has been confirmed under the conditions specified above.

Optimum operating conditions should be selected with careful confirmation for no occurrence of any maximum rating violation (T_{vj} , V_{CES} , etc.) or any unexpected malfunction (arm-short-through, oscillation, etc.) at the actual application conditions.

CHIP LOCATION (Top view)

Dimension in mm, typ value

[Top View]

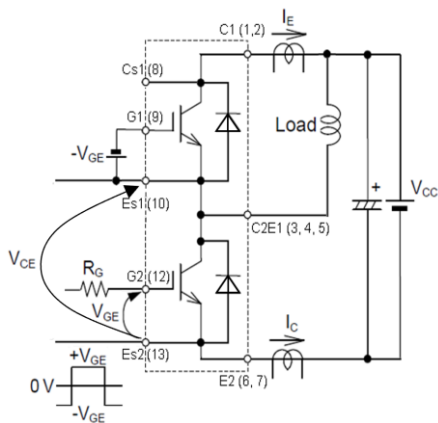


Tr1/Tr2: IGBT, Di1/Di2: FWD, Th: NTC thermistor

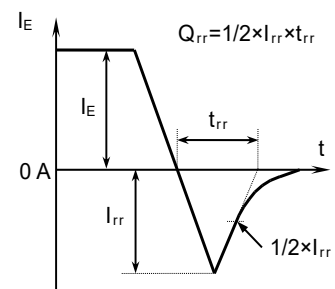
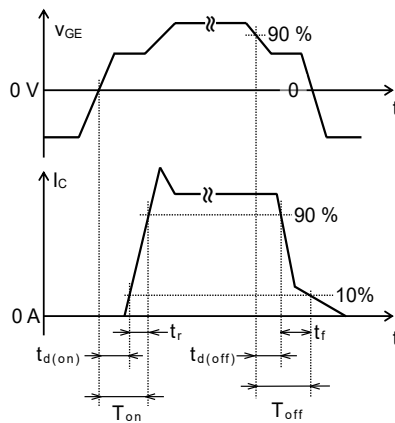
CM1800DW-24ME

HIGH POWER SWITCHING USE
INSULATED TYPE

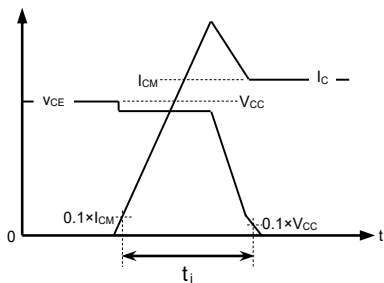
TEST CIRCUIT AND WAVEFORMS



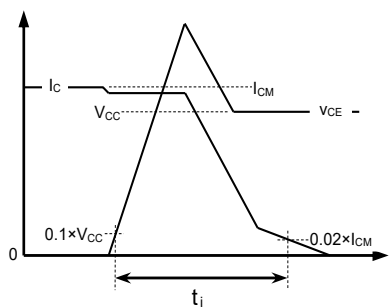
Switching characteristics test circuit and waveforms



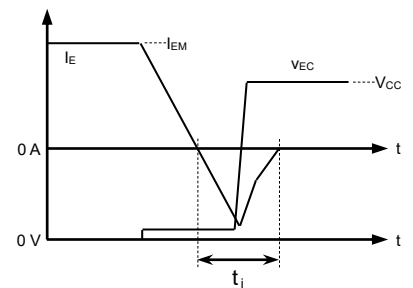
t_{rr} , Q_{rr} characteristics test waveform



IGBT Turn-on switching energy

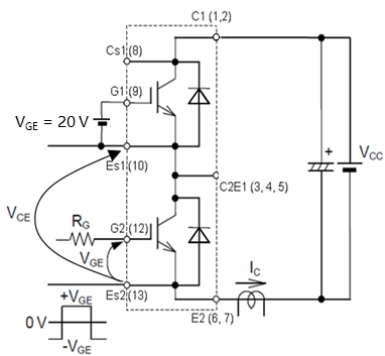


IGBT Turn-off switching energy

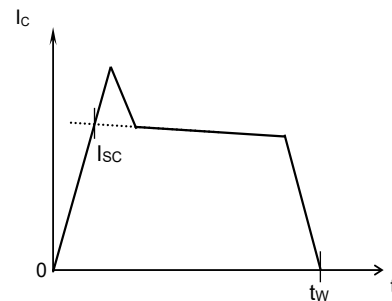


FWD Reverse recovery energy

Switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

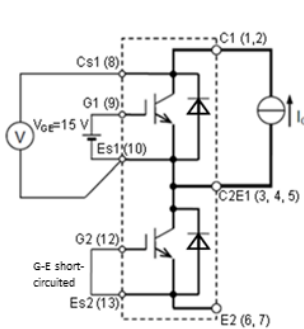


Short-circuit characteristics test circuit



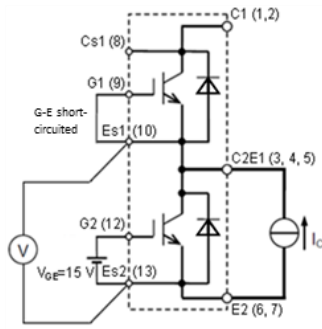
I_{sc} characteristics test waveform

TEST CIRCUIT

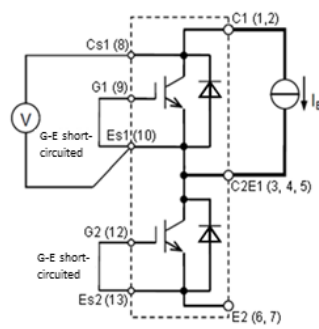


Tr1

V_{CEsat} characteristics test circuit

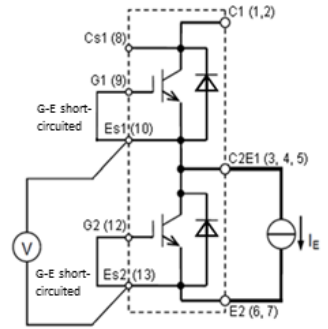


Tr2



Di1

V_{CE} characteristics test circuit



Di2

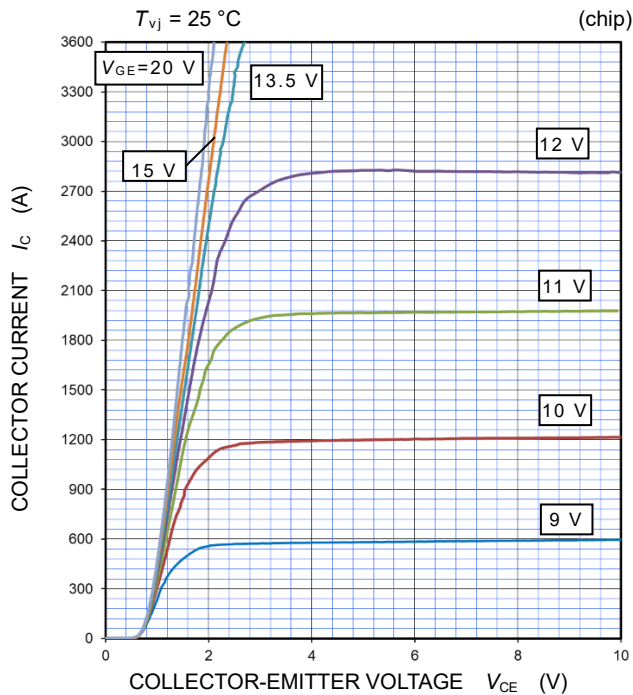
CM1800DW-24ME

HIGH POWER SWITCHING USE
INSULATED TYPE

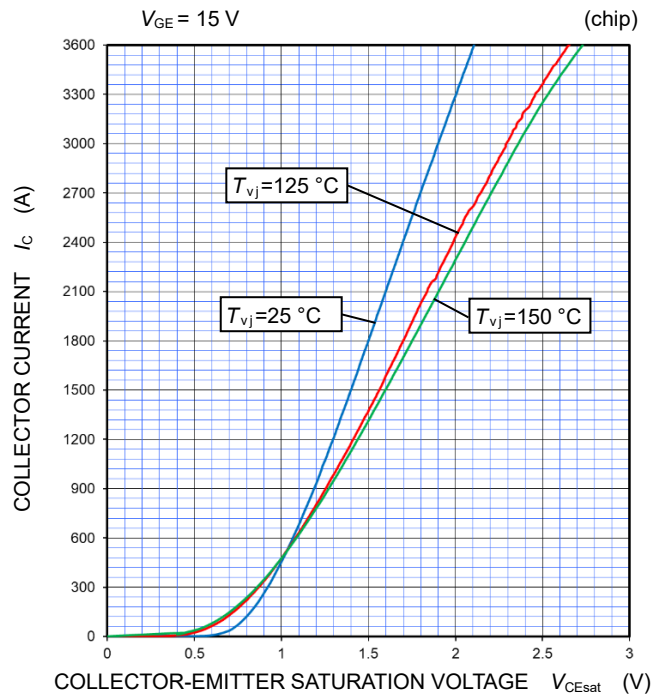
PERFORMANCE CURVES

INVERTER PART

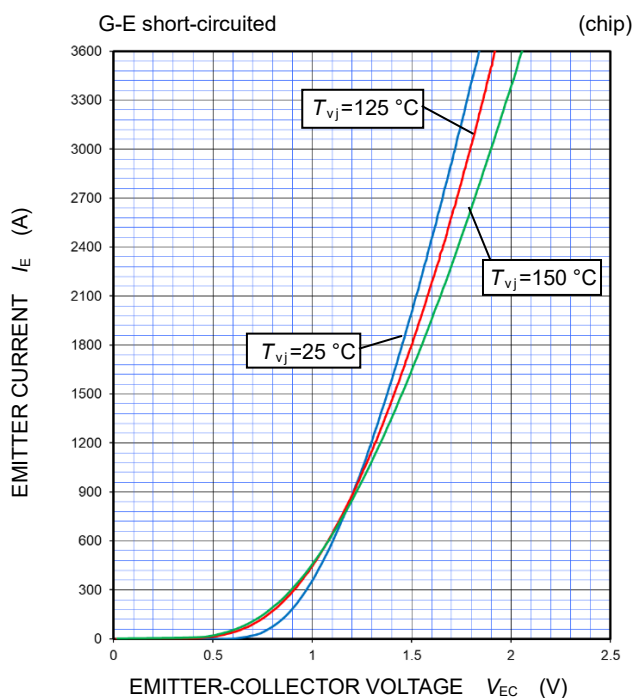
OUTPUT CHARACTERISTICS
(TYPICAL)



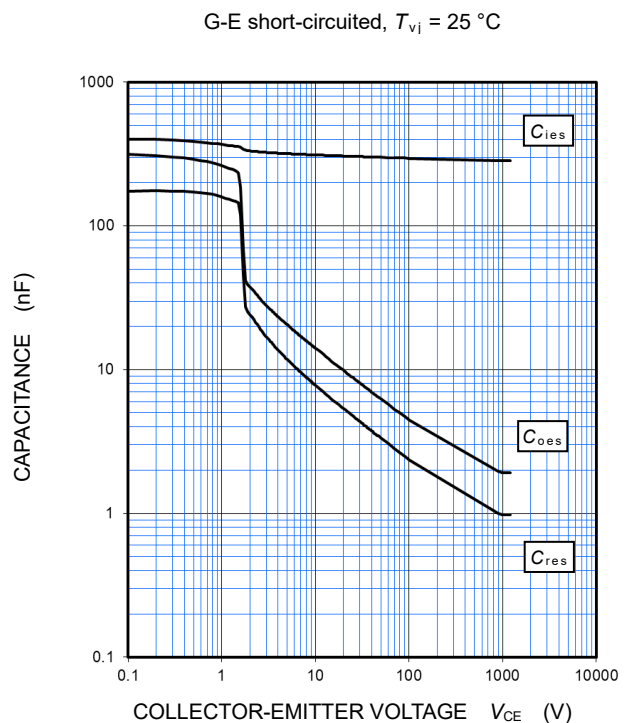
COLLECTOR-EMITTER SATURATION VOLTAGE
CHARACTERISTICS
(TYPICAL)



FREE WHEELING DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



CAPACITANCE CHARACTERISTICS
(TYPICAL)



CM1800DW-24ME

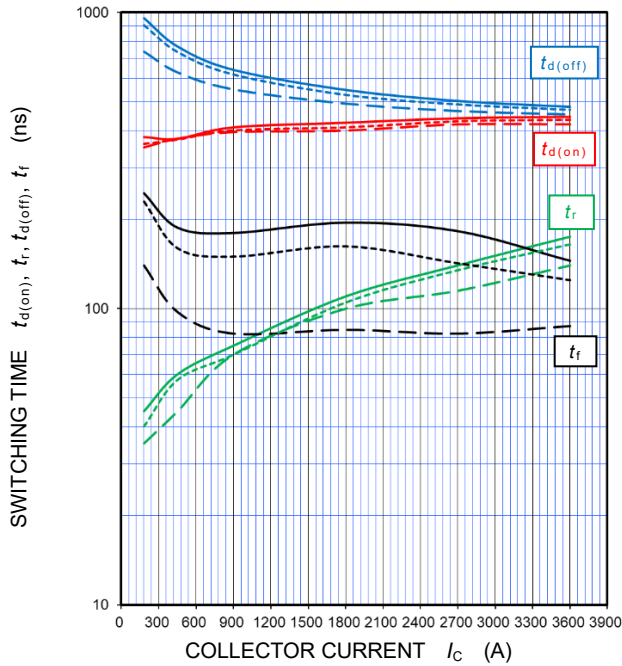
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

INVERTER PART

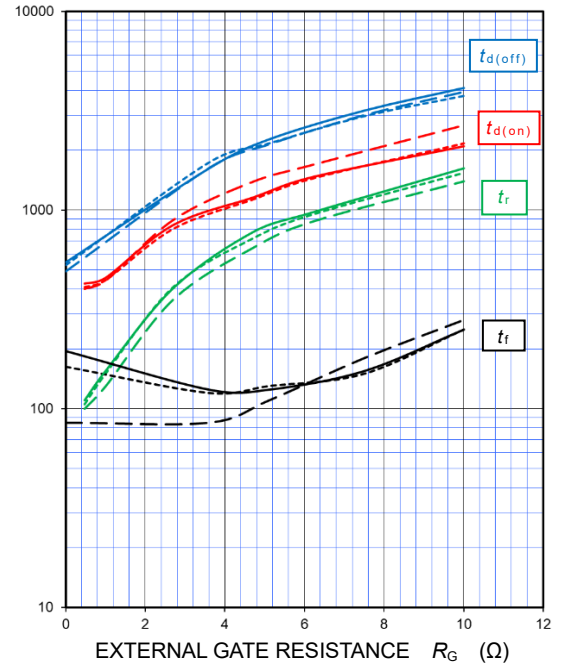
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC} = 600\text{ V}$, $R_{Gon} = 0.47\ \Omega$, $R_{Goff} = 0\ \Omega$, $V_{GE} = \pm 15\text{ V}$,
 $L_{\sigma} = 15\text{ nH}$, INDUCTIVE LOAD,
—: $T_{vj} = 150\text{ }^{\circ}\text{C}$, - - -: $T_{vj} = 125\text{ }^{\circ}\text{C}$, - · - ·: $T_{vj} = 25\text{ }^{\circ}\text{C}$



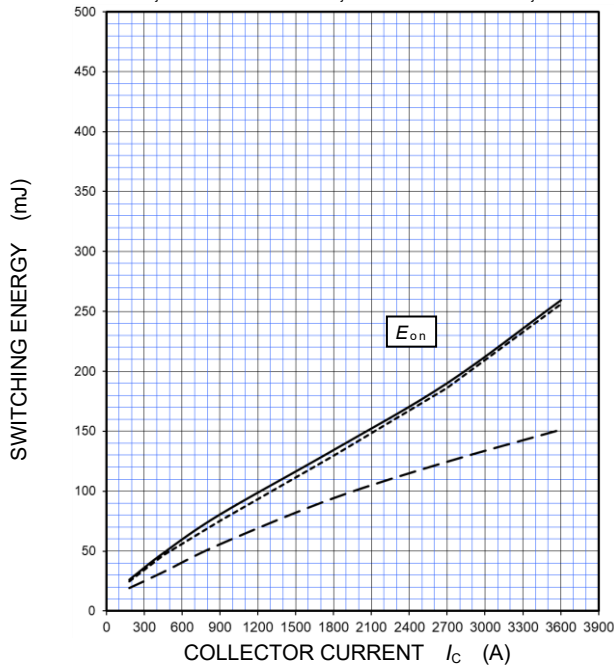
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC} = 600\text{ V}$, $I_C/I_E = 1800\text{ A}$, $V_{GE} = \pm 15\text{ V}$, $L_{\sigma} = 15\text{ nH}$,
INDUCTIVE LOAD,
—: $T_{vj} = 150\text{ }^{\circ}\text{C}$, - - -: $T_{vj} = 125\text{ }^{\circ}\text{C}$, - · - ·: $T_{vj} = 25\text{ }^{\circ}\text{C}$



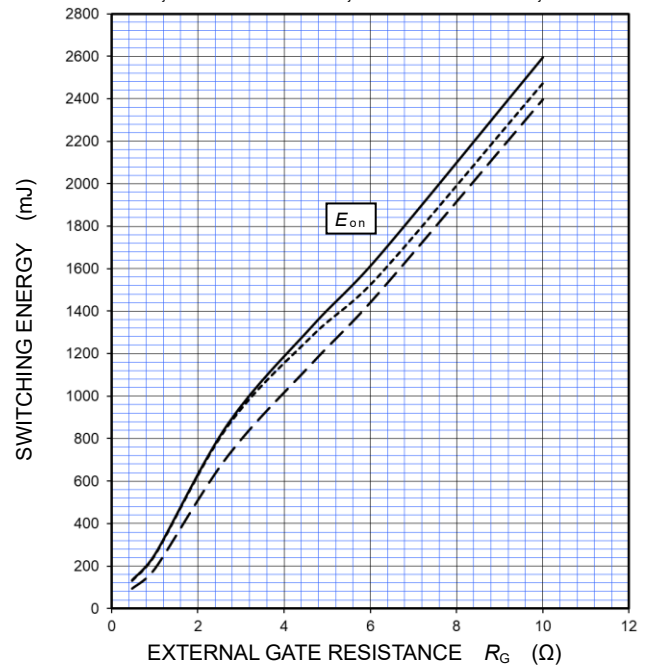
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC} = 600\text{ V}$, $R_{Gon} = 0.47\ \Omega$, $V_{GE} = \pm 15\text{ V}$, $L_{\sigma} = 15\text{ nH}$
INDUCTIVE LOAD, PER PULSE
—: $T_{vj} = 150\text{ }^{\circ}\text{C}$, - - -: $T_{vj} = 125\text{ }^{\circ}\text{C}$, - · - ·: $T_{vj} = 25\text{ }^{\circ}\text{C}$



HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC} = 600\text{ V}$, $I_C = 1800\text{ A}$, $V_{GE} = \pm 15\text{ V}$, $L_{\sigma} = 15\text{ nH}$
INDUCTIVE LOAD, PER PULSE
—: $T_{vj} = 150\text{ }^{\circ}\text{C}$, - - -: $T_{vj} = 125\text{ }^{\circ}\text{C}$, - · - ·: $T_{vj} = 25\text{ }^{\circ}\text{C}$



CM1800DW-24ME

HIGH POWER SWITCHING USE
INSULATED TYPE

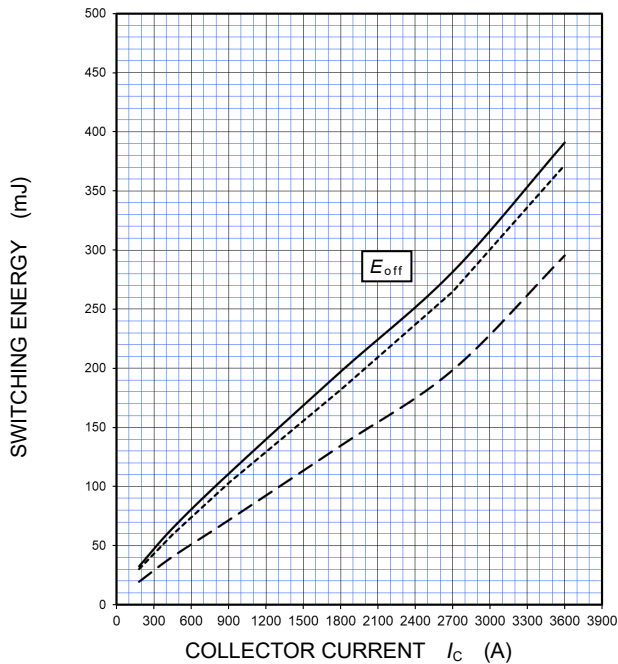
PERFORMANCE CURVES

INVERTER PART

HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC} = 600\text{ V}$, $R_{Goff} = 0\ \Omega$, $V_{GE} = \pm 15\text{ V}$, $L_{\sigma} = 15\text{ nH}$
INDUCTIVE LOAD, PER PULSE

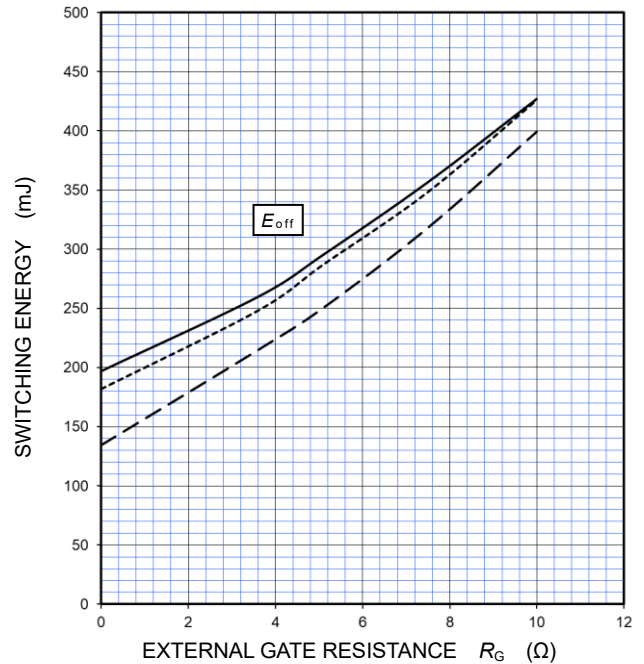
—: $T_{vj} = 150\text{ }^{\circ}\text{C}$, - - - -: $T_{vj} = 125\text{ }^{\circ}\text{C}$, - - -: $T_{vj} = 25\text{ }^{\circ}\text{C}$



HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC} = 600\text{ V}$, $I_C = 1800\text{ A}$, $V_{GE} = \pm 15\text{ V}$, $L_{\sigma} = 15\text{ nH}$
INDUCTIVE LOAD, PER PULSE

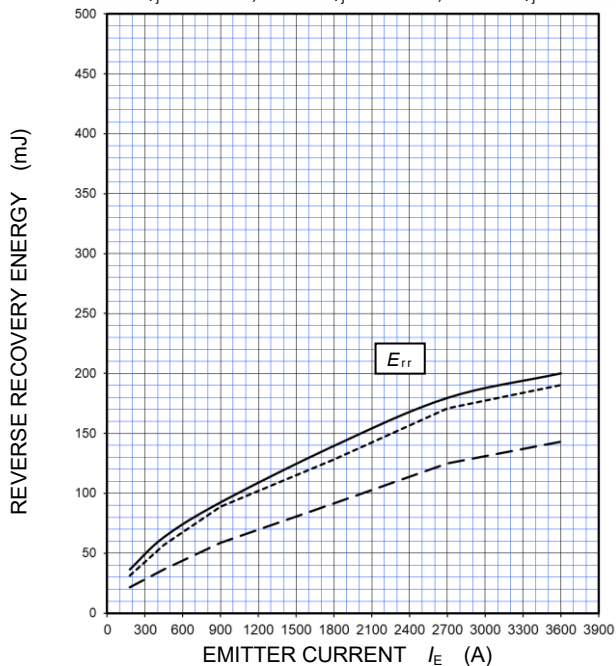
—: $T_{vj} = 150\text{ }^{\circ}\text{C}$, - - - -: $T_{vj} = 125\text{ }^{\circ}\text{C}$, - - -: $T_{vj} = 25\text{ }^{\circ}\text{C}$



HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC} = 600\text{ V}$, $R_{Gon} = 0.47\ \Omega$, $V_{GE} = \pm 15\text{ V}$, $L_{\sigma} = 15\text{ nH}$
INDUCTIVE LOAD, PER PULSE

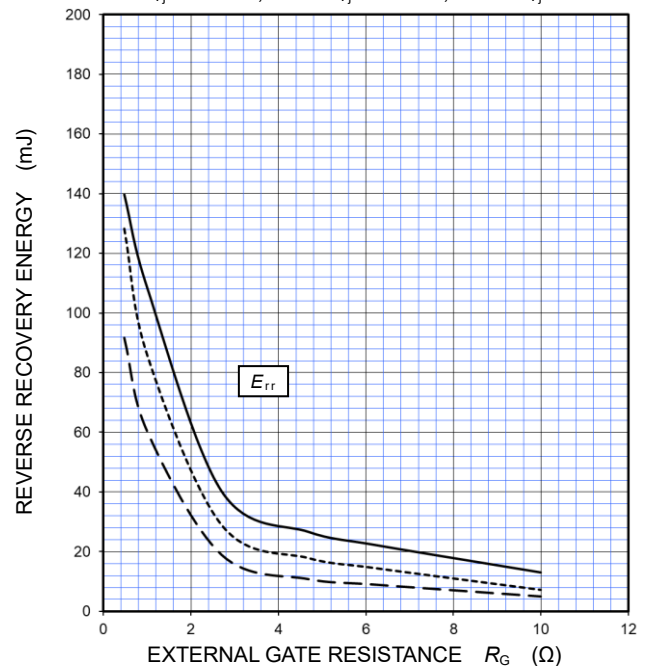
—: $T_{vj} = 150\text{ }^{\circ}\text{C}$, - - - -: $T_{vj} = 125\text{ }^{\circ}\text{C}$, - - -: $T_{vj} = 25\text{ }^{\circ}\text{C}$



HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC} = 600\text{ V}$, $I_E = 1800\text{ A}$, $V_{GE} = \pm 15\text{ V}$, $L_{\sigma} = 15\text{ nH}$
INDUCTIVE LOAD, PER PULSE

—: $T_{vj} = 150\text{ }^{\circ}\text{C}$, - - - -: $T_{vj} = 125\text{ }^{\circ}\text{C}$, - - -: $T_{vj} = 25\text{ }^{\circ}\text{C}$



CM1800DW-24ME

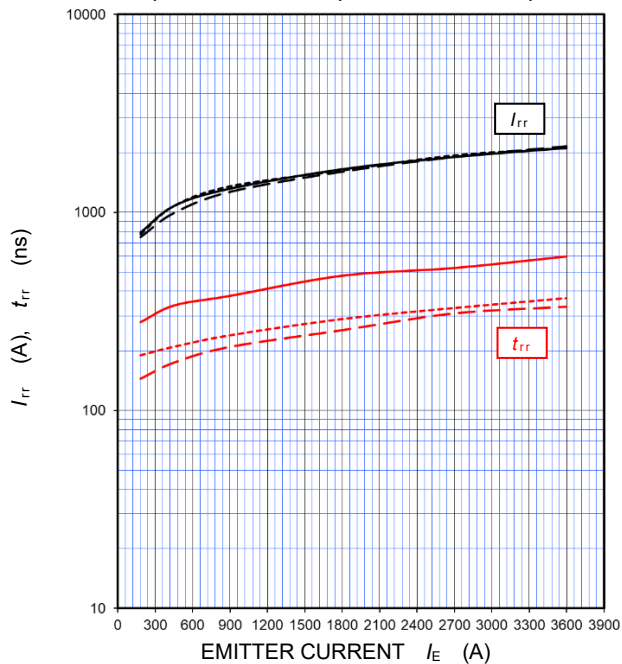
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

INVERTER PART

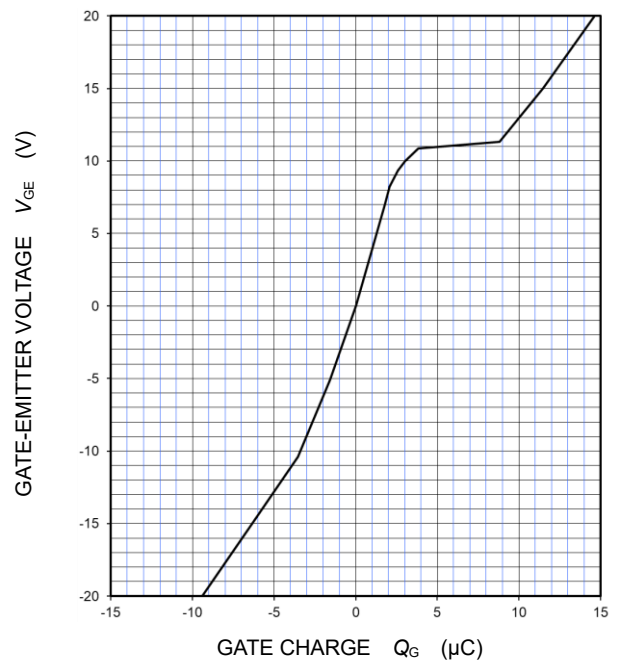
**FREE WHEELING DIODE
REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)**

$V_{CC} = 600\text{ V}$, $R_{Gon} = 0.47\ \Omega$, $V_{GE} = \pm 15\text{ V}$, INDUCTIVE LOAD
 —: $T_{vj} = 150\text{ }^\circ\text{C}$, - - - -: $T_{vj} = 125\text{ }^\circ\text{C}$, - - - -: $T_{vj} = 25\text{ }^\circ\text{C}$



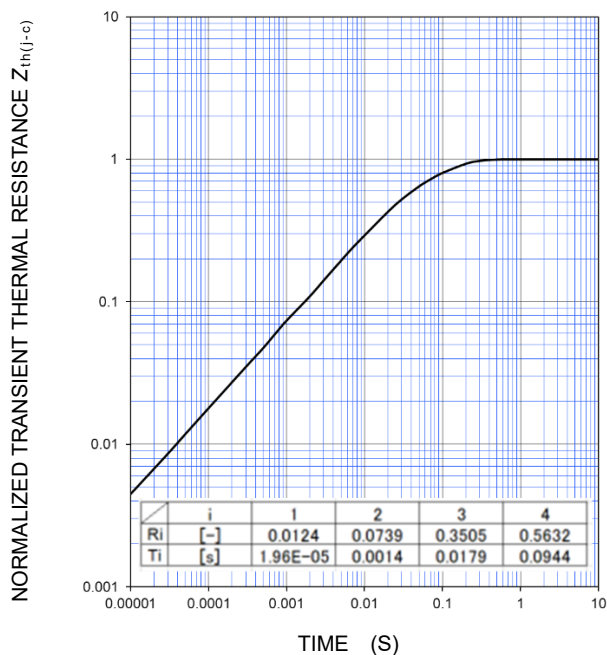
**GATE CHARGE CHARACTERISTICS
(TYPICAL)**

$V_{CC} = 600\text{ V}$, $I_C = 1800\text{ A}$, $T_{vj} = 25\text{ }^\circ\text{C}$



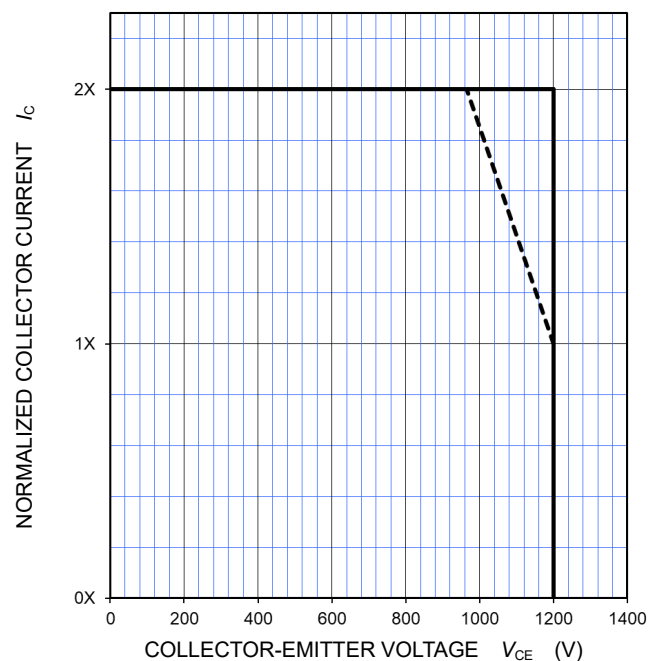
**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS
(MAXIMUM)**

Single pulse, $T_C = 25\text{ }^\circ\text{C}$
 $R_{th(j-c)Q} = 24\text{ K/kW}$, $R_{th(j-c)D} = 39\text{ K/kW}$



**TURN-OFF SWITCHING SAFE OPERATING AREA
(REVERSE BIAS SAFE OPERATING AREA)
(MAXIMUM)**

$V_{CC} \leq 850\text{ V}$, $R_{G(off)} = 0\ \Omega$, $V_{GE} = \pm 15\text{ V}$
 —: $T_{vj} = 150\text{ }^\circ\text{C}$, - - - -: $T_{vj} = 175\text{ }^\circ\text{C}$



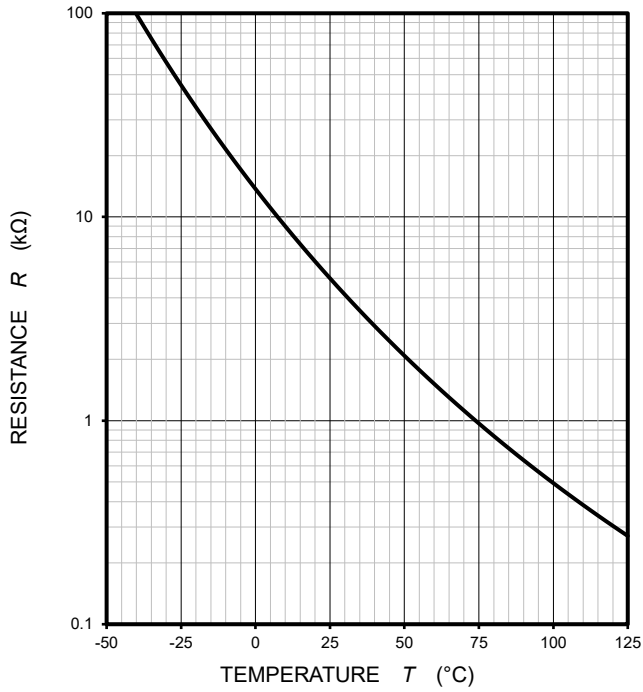
CM1800DW-24ME

HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

NTC thermistor part

TEMPERATURE CHARACTERISTICS
(TYPICAL)



Note: The characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

CM1800DW-24ME

HIGH POWER SWITCHING USE
INSULATED TYPE

Important Notice

The information contained in this datasheet shall in no event be regarded as a guarantee of conditions or characteristics. This product has to be used within its specified maximum ratings, and is subject to customer's compliance with any applicable legal requirement, norms and standards.

Except as otherwise explicitly approved by Mitsubishi Electric Corporation in a written document signed by authorized representatives of Mitsubishi Electric Corporation, our products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.

In usage of power semiconductor, there is always the possibility that trouble may occur with them by the reliability lifetime such as Power Cycle, Thermal Cycle or others, or when used under special circumstances (e.g. condensation, high humidity, dusty, salty, highlands, environment with lots of organic matter / corrosive gas / explosive gas, or situations which terminals of semiconductor products receive strong mechanical stress). Therefore, please pay sufficient attention to such circumstances. Further, depending on the technical requirements, our semiconductor products may contain environmental regulation substances, etc. If there is necessity of detailed confirmation, please contact our nearest sales branch or distributor.

The contents or data contained in this datasheet are exclusively intended for technically trained staff. Customer's technical departments should take responsibility to evaluate the suitability of Mitsubishi Electric Corporation product for the intended application and the completeness of the product data with respect to such application. In the customer's research and development, please evaluate it not only with a single semiconductor product but also in the entire system, and judge whether it's applicable. As required, pay close attention to the safety design by installing appropriate fuse or circuit breaker between a power supply and semiconductor products to prevent secondary damage. Please also pay attention to the application note and the related technical information.

CM1800DW-24ME

HIGH POWER SWITCHING USE
INSULATED TYPE

Keep safety first in your circuit designs!

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

- These materials are intended as a reference to assist our customers in the selection of the Mitsubishi Electric Semiconductor product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Mitsubishi Electric Corporation or a third party.
- Mitsubishi Electric Corporation assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.
- All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Mitsubishi Electric Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact Mitsubishi Electric Corporation or an authorized Mitsubishi Electric Semiconductor product distributor for the latest product information before purchasing a product listed herein.
The information described here may contain technical inaccuracies or typographical errors. Mitsubishi Electric Corporation assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.
Please also pay attention to information published by Mitsubishi Electric Corporation by various means, including the Mitsubishi Electric Semiconductor home page (<http://www.MitsubishiElectric.com/semiconductor/>).
- When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Mitsubishi Electric Corporation assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.
- Mitsubishi Electric Corporation semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Electric Semiconductor product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
- The prior written approval of Mitsubishi Electric Corporation is necessary to reprint or reproduce in whole or in part these materials.
- If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.
Any diversion or re-export contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.
- Please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Electric Semiconductor product distributor for further details on these materials or the products contained therein.

Generally the listed company name and the brand name are the trademarks or registered trademarks of the respective companies.